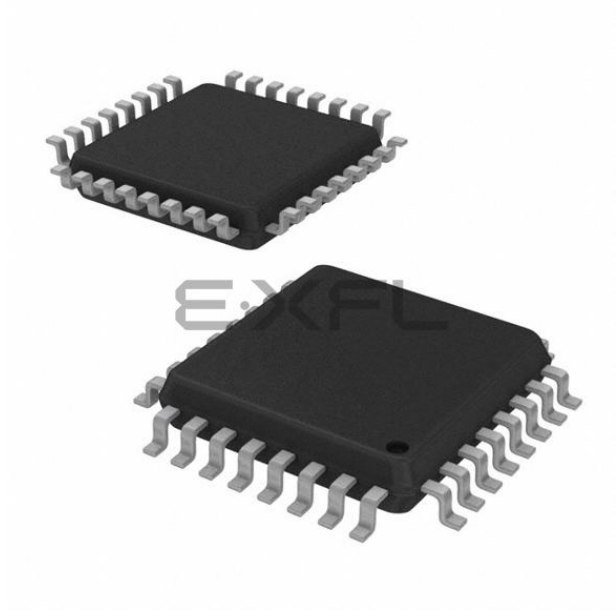

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What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Active
Core Processor	ARM® Cortex®-M4
Core Size	32-Bit Single-Core
Speed	72MHz
Connectivity	CANbus, I²C, IrDA, LINbus, SPI, UART/USART
Peripherals	DMA, I²S, POR, PWM, WDT
Number of I/O	25
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	2V ~ 3.6V
Data Converters	A/D 9x12b; D/A 3x12b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	32-LQFP
Supplier Device Package	32-LQFP (7x7)
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/stm32f303k8t6

- 96-bit unique ID
- All packages ECOPACK®2

Table 1. Device summary

Reference	Part number
STM32F303x6	STM32F303K6/C6/R6
STM32F303x8	STM32F303K8/C8/R8

1 Introduction

This datasheet provides the ordering information and the mechanical device characteristics of the STM32F303x6/8 microcontrollers.

This document should be read in conjunction with the STM32F303xx, STM32F358xx and STM32F328xx advanced ARM®-based 32-bit MCUs reference manual (RM00316) available from the STMicroelectronics website *www.st.com*.

For information on the Cortex®-M4 core with FPU, refer to:

- ARM® Cortex®-M4 Processor Technical Reference Manual available from the www.arm.com website.
- STM32F3xxx and STM32F4xxx Cortex®-M4 programming manual (PM0214) available from the *www.st.com* website.

2 Description

The STM32F303x6/8 family incorporates the high-performance ARM® Cortex®-M4 32-bit RISC core operating at up to 72 MHz frequency embedding a floating point unit (FPU), high-speed embedded memories (up to 64 Kbytes of Flash memory, 12 Kbytes of SRAM), and an extensive range of enhanced I/Os and peripherals connected to two APB buses.

The STM32F303x6/8 microcontrollers offer up to two fast 12-bit ADCs (5 Msps), up to three ultra-fast comparators, an operational amplifier, three DAC channels, a low-power RTC, one general-purpose, 32-bit timer, one timer dedicated to motor control, and four general-purpose, 16-bit timers. They also feature standard and advanced communication interfaces: one I^2C, one SPI, up to three USARTs and one CAN.

The STM32F303x6/8 family operates in the –40 to +85 °C and –40 to +105 °C temperature ranges from a 2.0 to 3.6 V power supply. A comprehensive set of power-saving modes allows the design of low-power applications.

The STM32F303x6/8 family offers devices in 32, and 64-pin packages.

Depending on the device chosen, different sets of peripherals are included.

remains in reset mode when the monitored supply voltage is below a specified threshold, $V_{POR/PDR}$, without the need for an external reset circuit.

- The POR monitors only the V_{DD} supply voltage. During the startup phase it is required that V_{DDA} should arrive first and be greater than or equal to V_{DD}.
- The PDR monitors both the V_{DD} and V_{DDA} supply voltages, however the V_{DDA} power supply supervisor can be disabled (by programming a dedicated Option bit) to reduce the power consumption if the application design ensures that V_{DDA} is higher than or equal to V_{DD}.

The device features an embedded programmable voltage detector (PVD) that monitors the V_{DD} power supply and compares it to the V_{PVD} threshold. An interrupt can be generated when V_{DD} drops below the V_{PVD} threshold and/or when V_{DD} is higher than the V_{PVD} threshold. The interrupt service routine can then generate a warning message and/or put the MCU into a safe state. The PVD is enabled by software.

3.4.3 Voltage regulator

The regulator has three operation modes: main (MR), low-power (LPR), and power-down.

- The MR mode is used in the nominal regulation mode (Run)
- The LPR mode is used in Stop mode.
- The power-down mode is used in Standby mode: the regulator output is in high impedance, and the kernel circuitry is powered down thus inducing zero consumption.

The voltage regulator is always enabled after reset. It is disabled in Standby mode.

3.4.4 Low-power modes

The STM32F303x6/8 supports three low-power modes to achieve the best compromise between low power consumption, short startup time and available wakeup sources:

- **Sleep mode**

  In Sleep mode, only the CPU is stopped. All peripherals continue to operate and can wake up the CPU when an interrupt/event occurs.

- **Stop mode**

  Stop mode achieves the lowest power consumption while retaining the content of SRAM and registers. All clocks in the 1.8 V domain are stopped, the PLL, the HSI RC and the HSE crystal oscillators are disabled. The voltage regulator can also be put either in normal or in low-power mode.

  The device can be woken up from Stop mode by any of the EXTI line. The EXTI line source can be one of the 16 external lines, the PVD output, the RTC alarm, COMPx, I^2C or USARTx.

- **Standby mode**

  The Standby mode is used to achieve the lowest power consumption. The internal voltage regulator is switched off so that the entire 1.8 V domain is powered off. The PLL, the HSI RC and the HSE crystal oscillators are also switched off. After entering Standby mode, SRAM and register contents are lost except for registers in the Backup domain and Standby circuitry.

  The device exits Standby mode when an external reset (NRST pin), an IWDG reset, a rising edge on the WKUP pin, or an RTC alarm occurs.

Note: The RTC, the IWDG, and the corresponding clock sources are not stopped by entering Stop or Standby mode.

high-speed APB domains is 72 MHz, while the maximum allowed frequency of the low-speed APB domain is 36 MHz.

TIM1 maximum frequency is 144 MHz.

3.7 General-purpose inputs/outputs (GPIOs)

Each of the GPIO pins can be configured by software as output (push-pull or open-drain), as input (with or without pull-up or pull-down) or as peripheral alternate function. Most of the GPIO pins are shared with digital or analog alternate functions. All GPIOs are high current capable except for analog inputs.

The I/Os alternate function configuration can be locked if needed, following a specific sequence to avoid spurious writing to the I/Os registers.

Fast I/O handling allows I/O toggling up to 36 MHz.

3.8 Direct memory access (DMA)

The flexible general-purpose DMA is able to manage memory-to-memory, peripheral-to-memory and memory-to-peripheral transfers. The DMA controller supports circular buffer management, avoiding the generation of interrupts when the controller reaches the end of the buffer.

Each of the 7 DMA channels is connected to dedicated hardware DMA requests, with software trigger support for each channel. Configuration is done by software and transfer sizes between source and destination are independent.

The DMA can be used with the main peripherals: SPI, I^2C, USART, general-purpose timers, DAC and ADC.

3.9 Interrupts and events

3.9.1 Nested vectored interrupt controller (NVIC)

The STM32F303x6/8 devices embed a nested vectored interrupt controller (NVIC) able to handle up to 60 interrupt channels, that can be masked and 16 priority levels.

The NVIC benefits are the following:

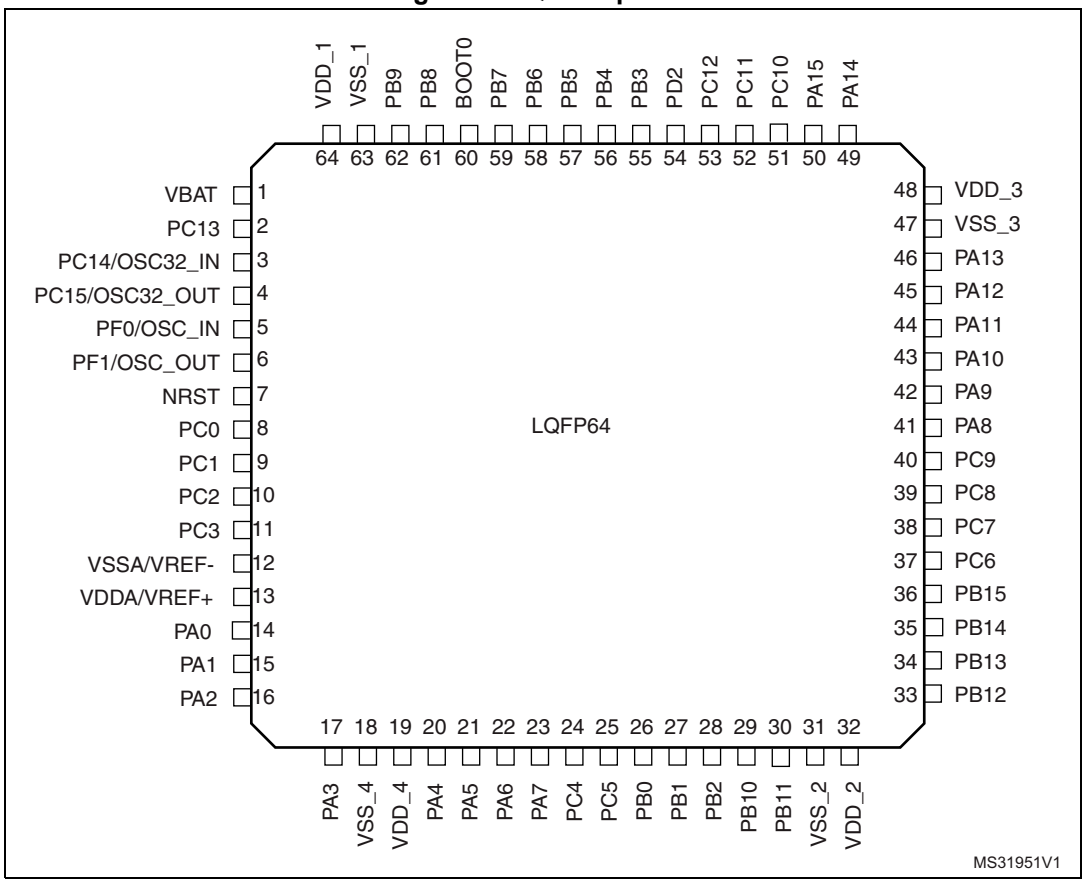
- Closely coupled NVIC gives low latency interrupt processing
- Interrupt entry vector table address passed directly to the core
- Closely coupled NVIC core interface
- Allows early processing of interrupts
- Processing of late arriving higher priority interrupts
- Support for tail chaining
- Processor state automatically saved
- Interrupt entry restored on interrupt exit with no instruction overhead

The NVIC hardware block provides flexible interrupt management features with minimal interrupt latency.

3.9.2 Extended interrupt/event controller (EXTI)

The external interrupt/event controller consists of 27 edge detector lines used to generate interrupt/event requests and wake-up the system. Each line can be independently configured to select the trigger event (rising edge, falling edge, both) and can be masked

Figure 6. LQFP64 pinout



6.3 Operating conditions

6.3.1 General operating conditions

Table 20. General operating conditions

Symbol	Parameter	Conditions	Min.	Max.	Unit
f_{HCLK}	Internal AHB clock frequency	-	0	72	MHz
f_{PCLK1}	Internal APB1 clock frequency	-	0	36	
f_{PCLK2}	Internal APB2 clock frequency	-	0	72	
V_{DD}	Standard operating voltage	-	2	3.6	V
V_{DDA}	Analog operating voltage (OPAMP and DAC not used)	Must have a potential equal to or higher than V_{DD}	2	3.6	
	Analog operating voltage (OPAMP and DAC used)		2.4	3.6	
V_{BAT}	Backup operating voltage	-	1.65	3.6	V
V_{IN}	I/O input voltage	TC I/O	–0.3	V_{DD}+0.3	V
		TT I/O	-0.3	3.6	
		TTa I/O	–0.3	V_{DDA}+0.3	
		FT and FTf I/O(1)	–0.3	5.5	
		BOOT0	0	5.5	
PD	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(2)	LQFP64	-	444	mW
PD	Power dissipation at T_A = 85 °C for suffix 6 or T_A = 105 °C for suffix 7(3)	LQFP48	-	364	mW
T_A	Ambient temperature for 6 suffix version	Maximum power dissipation	–40	85	°C
		Low power dissipation(4)	–40	105	
	Ambient temperature for 7 suffix version	Maximum power dissipation	–40	105	°C
		Low power dissipation(4)	–40	125	
T_J	Junction temperature range	6 suffix version	–40	105	°C
		7 suffix version	–40	125	

1. To sustain a voltage higher than V_{DD}+0.3 V, the internal pull-up/pull-down resistors must be disabled.
2. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see *Section 7.5: Thermal characteristics*).
3. If T_A is lower, higher P_D values are allowed as long as T_J does not exceed T_{Jmax} (see *Section 7.5: Thermal characteristics*).
4. In low power dissipation state, T_A can be extended to this range as long as T_J does not exceed T_{Jmax} (see *Section 7.5: Thermal characteristics*).

Table 27. Typical and maximum current consumption from the V_{DDA} supply

Symbol	Parameter	Conditions (1)	f_{HCLK}	V_{DDA} = 2.4 V				V_{DDA} = 3.6 V				Unit
				Typ.	Max. @ T_A(2)			Typ.	Max. @ T_A(2)			
					25 °C	85 °C	105 °C		25 °C	85 °C	105 °C	
I_{DDA}	Supply current in Run/Sleep mode, code executing from Flash or RAM	HSE bypass	72 MHz	224	252(3)	265	269(3)	245	272(3)	288	295(3)	µA
			64 MHz	196	225	237	241	214	243	257	263	
			48 MHz	147	174	183	186	159	186	196	201	
			32 MHz	100	126	133	135	109	133	142	145	
			24 MHz	79	102	107	108	85	108	113	116	
			8 MHz	3	5	5	6	4	6	6	7	
			1 MHz	3	5	5	6	3	5	6	6	
		HSI clock	64 MHz	259	288	304	309	285	315	332	338	
			48 MHz	208	239	251	254	230	258	271	277	
			32 MHz	162	190	198	202	179	206	216	219	
			24 MHz	140	168	175	178	155	181	188	191	
			8 MHz	62	85	88	89	71	94	96	98	

1. Current consumption from the V_{DDA} supply is independent of whether the peripherals are on or off. Furthermore when the PLL is off, I_{DDA} is independent from the frequency.
2. Data based on characterization results, not tested in production.
3. Data based characterization results and tested in production with code executing from RAM.

Table 28. Typical and maximum V_{DD} consumption in Stop and Standby modes

Symbol	Parameter	Conditions	Typ. @V_{DD} (V_{DD}=V_{DDA})						Max.(1)			Unit
			2.0 V	2.4 V	2.7 V	3.0 V	3.3 V	3.6 V	T_A = 25 °C	T_A = 85 °C	T_A = 105 °C	
I_{DD}	Supply current in Stop mode	Regulator in run mode, all oscillators OFF	17.51	17.68	17.84	18.17	18.57	19.39	30.6	232.5	612.2	µA
		Regulator in low-power mode, all oscillators OFF	6.44	6.51	6.60	6.73	6.96	7.20	20.0	246.4	585.0	
	Supply current in Standby mode	LSI ON and IWDG ON	0.73	0.89	1.02	1.14	1.28	1.44	-	-	-	
		LSI OFF and IWDG OFF	0.55	0.66	0.75	0.85	0.93	1.01	4.9	7.0	7.9	

1. Data based on characterization results, not tested in production unless otherwise specified.

The test pin is configured in push-pull output mode and is toggled by software at a fixed frequency.

Table 34. Switching output I/O current consumption

Symbol	Parameter	Conditions[1]	I/O toggling frequency (f_{SW})	Typ.	Unit
I_{SW}	I/O current consumption	V_{DD} =3.3 V C_{ext} = 0 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.90	mA
			4 MHz	0.93	
			8 MHz	1.16	
			18 MHz	1.60	
			36 MHz	2.51	
		V_{DD} = 3.3 V C_{ext} = 10 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	0.93	
			4 MHz	1.06	
			8 MHz	1.47	
			18 MHz	2.26	
			36 MHz	3.39	
		V_{DD} = 3.3 V C_{ext} = 22 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.03	
			4 MHz	1.30	
			8 MHz	1.79	
			18 MHz	3.01	
			36 MHz	5.99	
		V_{DD} = 3.3 V C_{ext} = 33 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.10	
			4 MHz	1.31	
			8 MHz	2.06	
			18 MHz	3.47	
			36 MHz	8.35	
		V_{DD} = 3.3 V C_{ext} = 47 pF $C = C_{INT} + C_{EXT} + C_S$	2 MHz	1.20	
			4 MHz	1.54	
			8 MHz	2.46	
			18 MHz	4.51	
			36 MHz	9.98	

1. CS = 5 pF (estimated value).

Table 35. Peripheral current consumption (continued)

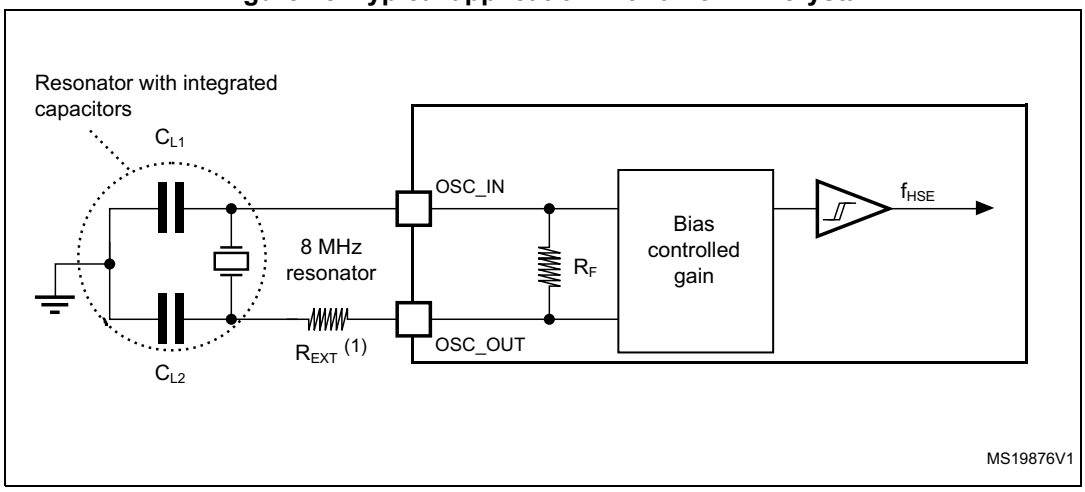
Peripheral	Typical consumption(1)	Unit
	I_{DD}	
CAN	31.3	-
PWR	4.7	-
DAC	15.4	-
DAC2	8.6	-
SPI1	8.2	-

1. The power consumption of the analog part (I_{DDA}) of peripherals such as ADC, DAC, Comparators, OpAmp etc. is not included. Refer to the tables of characteristics in the subsequent sections.
2. BusMatrix is automatically active when at least one master is ON (CPU or DMA1).
3. The APBx bridge is automatically active when at least one peripheral is ON on the same bus.

For C_{L1} and C_{L2}, it is recommended to use high-quality external ceramic capacitors in the 5 pF to 25 pF range (typ.), designed for high-frequency applications, and selected to match the requirements of the crystal or resonator (see *Figure 15*). C_{L1} and C_{L2} are usually the same size. The crystal manufacturer typically specifies a load capacitance which is the series combination of C_{L1} and C_{L2}. PCB and MCU pin capacitance must be included (10 pF can be used as a rough estimate of the combined pin and board capacitance) when sizing C_{L1} and C_{L2}.

Note: For information on selecting the crystal, refer to the application note AN2867 "Oscillator design guide for ST microcontrollers" available from the ST website www.st.com.

Figure 15. Typical application with an 8 MHz crystal



1. R_{EXT} value depends on the crystal characteristics.

Low-speed external clock generated from a crystal/ceramic resonator

The low-speed external (LSE) clock can be supplied with a 32.768 kHz crystal/ceramic resonator oscillator. All the information given in this paragraph are based on design simulation results obtained with typical external components specified in *Table 41*. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins to minimize output distortion and startup stabilization time. Refer to the crystal resonator manufacturer for more details on the resonator characteristics (frequency, package, accuracy).

Table 41. LSE oscillator characteristics (f_{LSE} = 32.768 kHz)

Symbol	Parameter	Conditions[1]	Min.[2]	Typ.	Max.[2]	Unit
I_{DD}	LSE current consumption	LSEDRV[1:0]=00 lower driving capability	-	0.5	0.9	µA
		LSEDRV[1:0]=10 medium low driving capability	-	-	1	
		LSEDRV[1:0]=01 medium high-driving capability	-	-	1.3	
		LSEDRV[1:0]=11 higher-driving capability	-	-	1.6	
g_m	Oscillator transconductance	LSEDRV[1:0]=00 lower-driving capability	5	-	-	µA/V
		LSEDRV[1:0]=10 medium low-driving capability	8	-	-	
		LSEDRV[1:0]=01 medium high-driving capability	15	-	-	
		LSEDRV[1:0]=11 higher-driving capability	25	-	-	
$t_{SU(LSE)}$[3]	Startup time	V_{DD} is stabilized	-	2	-	s

1. Refer to the note and caution paragraphs below the table, and to the application note AN2867 “Oscillator design guide for ST microcontrollers”.
2. Guaranteed by design, not tested in production.
3. $t_{SU(LSE)}$ is the startup time measured from the moment it is enabled (by software) to a stabilized 32.768 kHz oscillation is reached. This value is measured for a standard crystal and it can vary significantly with the crystal manufacturer.

Note: For information on selecting the crystal, refer to the application note AN2867 “Oscillator design guide for ST microcontrollers” available from the ST website www.st.com.

6.3.10 Memory characteristics

Flash memory

The characteristics are given at T_A = –40 to 105 °C unless otherwise specified.

Table 45. Flash memory characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.(1)	Unit
t_{prog}	16-bit programming time	T_A = –40 to +105 °C	40	53.5	60	µs
t_{ERASE}	Page (2 KB) erase time	T_A = –40 to +105 °C	20	-	40	ms
t_{ME}	Mass erase time	T_A = –40 to +105 °C	20	-	40	ms
I_{DD}	Supply current	Write mode	-	-	10	mA
		Erase mode	-	-	12	mA

1. Guaranteed by design, not tested in production.

Table 46. Flash memory endurance and data retention

Symbol	Parameter	Conditions	Value	Unit
			Min.(1)	
N_{END}	Endurance	TA = –40 to +85 °C (6 suffix versions) TA = –40 to +105 °C (7 suffix versions)	10	kcycles
t_{RET}	Data retention	1 kcycle(2) at T_A = 85 °C	30	Years
		1 kcycle(2) at T_A = 105 °C	10	
		10 kcycles(2) at T_A = 55 °C	20	

1. Data based on characterization results, not tested in production.
2. Cycling performed over the whole temperature range.

6.3.11 EMC characteristics

Susceptibility tests are performed on a sample basis during device characterization.

Functional EMS (electromagnetic susceptibility)

While a simple application is executed on the device (toggling 2 LEDs through I/O ports). the device is stressed by two electromagnetic events until a failure occurs. The failure is indicated by the LEDs:

- **Electrostatic discharge (ESD)** (positive and negative) is applied to all device pins until a functional disturbance occurs. This test is compliant with the IEC 61000-4-2 standard.
- **FTB**: A Burst of Fast Transient voltage (positive and negative) is applied to V_{DD} and V_{SS} through a 100 pF capacitor, until a functional disturbance occurs. This test is compliant with the IEC 61000-4-4 standard.

A device reset allows normal operations to be resumed.

The test results are given in *Table 47*. They are based on the EMS levels and classes defined in "*EMC design guide for ST microcontrollers*" application note (AN1709).

Table 59. I^2C analog filter characteristics(1)

Symbol	Parameter	Min.	Max.	Unit
t_{AF}	Maximum pulse width of spikes that are suppressed by the analog filter.	50(2)	260(3)	ns

1. Guaranteed by design, not tested in production.
2. Spikes with width below t_{AF}(min.) are filtered.
3. Spikes with width above t_{AF}(max.) are not filtered.

SPI characteristics

Unless otherwise specified, the parameters given in *Table 55* for SPI are derived from tests performed under ambient temperature, f_{PCLKx} frequency and V_{DD} supply voltage conditions summarized in *Table 20: General operating conditions*.

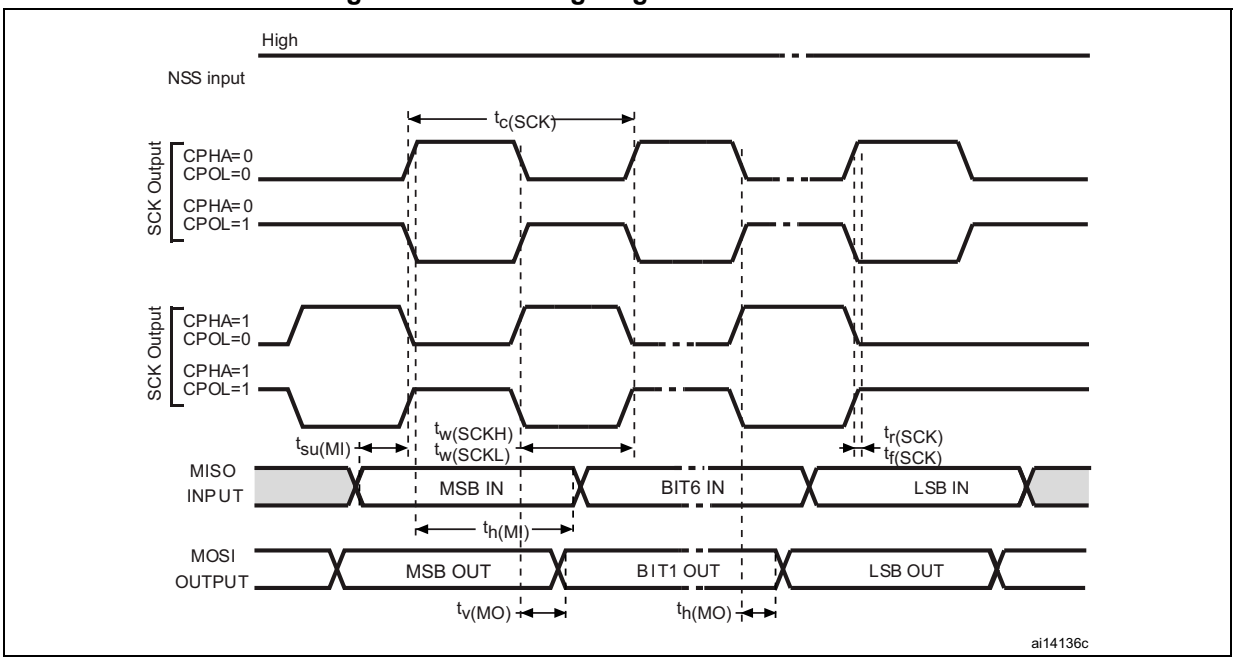
Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (NSS, SCK, MOSI, MISO for SPI).

Table 60. SPI characteristics(1)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{SCK} $1/t_{c(SCK)}$	SPI clock frequency	Master mode 2.7<V_{DD}<3.6	-	-	24	MHz
		Master mode 2<V_{DD}<3.6			18	
		Slave mode 2<V_{DD}<3.6			24	
		Slave mode transmitter/full duplex 2<V_{DD}<3.6			18(2)	
DuCy(SCK)	Duty cycle of SPI clock frequency	Slave mode	30	50	70	%
$t_{su(NSS)}$	NSS setup time	Slave mode, SPI presc = 2	4*Tpclk	-	-	ns
$t_{h(NSS)}$	NSS hold time	Slave mode, SPI presc = 2	2*Tpclk	-	-	
$t_{w(SCKH)}$ $t_{w(SCKL)}$	SCK high and low time	Master mode	Tpclk-2	Tpclk	Tpclk+2	
$t_{su(MI)}$	Data input setup time	Master mode	0	-	-	
$t_{su(SI)}$		Slave mode	3	-	-	
$t_{h(MI)}$	Data input hold time	Master mode	5	-	-	
$t_{h(SI)}$		Slave mode	1	-	-	
$t_{a(SO)}$	Data output access time	Slave mode	10	-	40	
$t_{dis(SO)}$	Data output disable time	Slave mode	10	-	17	
$t_{v(SO)}$	Data output valid time	Slave mode 2.7<V_{DD}<3.6V	-	12	20	
		Slave mode 2<V_{DD}<3.6V	-	12	27.5	
$t_{v(MO)}$		Master mode	-	1.5	5	
$t_{h(SO)}$	Data output hold time	Slave mode	7.5	-	-	
$t_{h(MO)}$		Master mode	0	-	-	

1. Data based on characterization results, not tested in production.
2. Maximum frequency in Slave transmitter mode is determined by the sum of tv(SO) and tsu(MI) which has to fit into SCK low or high phase preceding the SCK sampling edge. This value can be achieved when the SPI communicates with a master having tsu(MI) = 0 while Duty(SCK) = 50%.

Figure 26. SPI timing diagram - master mode(1)



1. Measurement points are done at $0.5V_{DD}$ and with external C_L = 30 pF.

CAN (controller area network) interface

Refer to *Section 6.3.14: I/O port characteristics* for more details on the input/output alternate function characteristics (CAN_TX and CAN_RX).

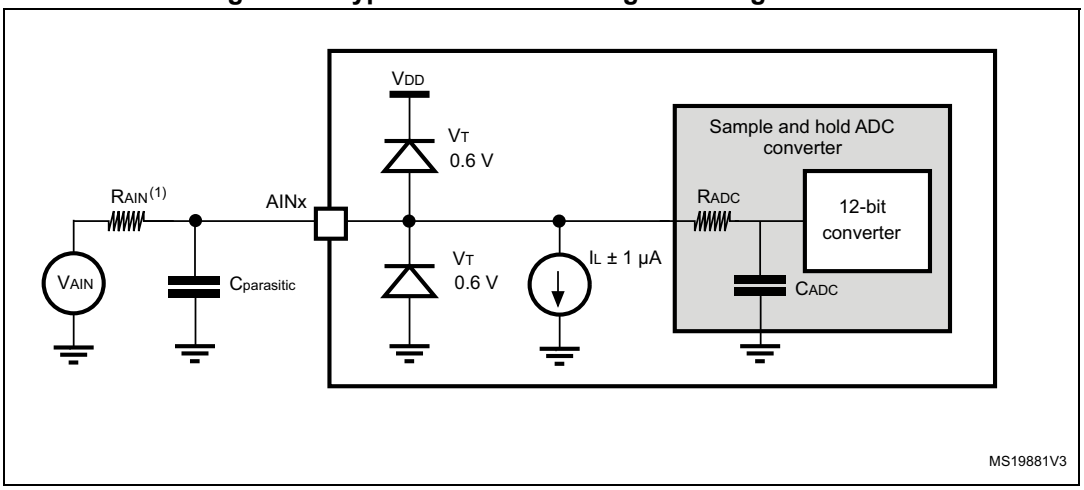
6.3.18 ADC characteristics

Unless otherwise specified, the parameters given in *Table 61* to *Table 64* are guaranteed by design, with conditions summarized in *Table 20*.

Table 61. ADC characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{DDA}	Analog supply voltage for ADC	-	2	-	3.6	V
I_{DDA}	ADC current consumption (*Figure 27*)	Single ended mode, 5 MSPS,	-	1011.3	1172.0	µA
		Single ended mode, 1 MSPS	-	214.7	322.3	
		Single ended mode, 200 KSPS	-	54.7	81.1	
		Differential mode,5 MSPS,	-	1061.5	1243.6	
		Differential mode, 1 MSPS	-	246.6	337.6	
		Differential mode, 200 KSPS	-	56.4	83.0	

Figure 29. Typical connection diagram using the ADC



1. Refer to *Table 61* for the values of R_{AIN}.
2. $C_{parasitic}$ represents the capacitance of the PCB (dependent on soldering and PCB layout quality) plus the pad capacitance (roughly 7 pF). A high $C_{parasitic}$ value will downgrade conversion accuracy. To remedy this, f_{ADC} should be reduced.

General PCB design guidelines

Power supply decoupling should be performed as shown in *Figure 10: Power-supply scheme*. The 10 nF capacitor should be ceramic (good quality) and it should be placed as close as possible to the chip.

6.3.19 DAC electrical specifications

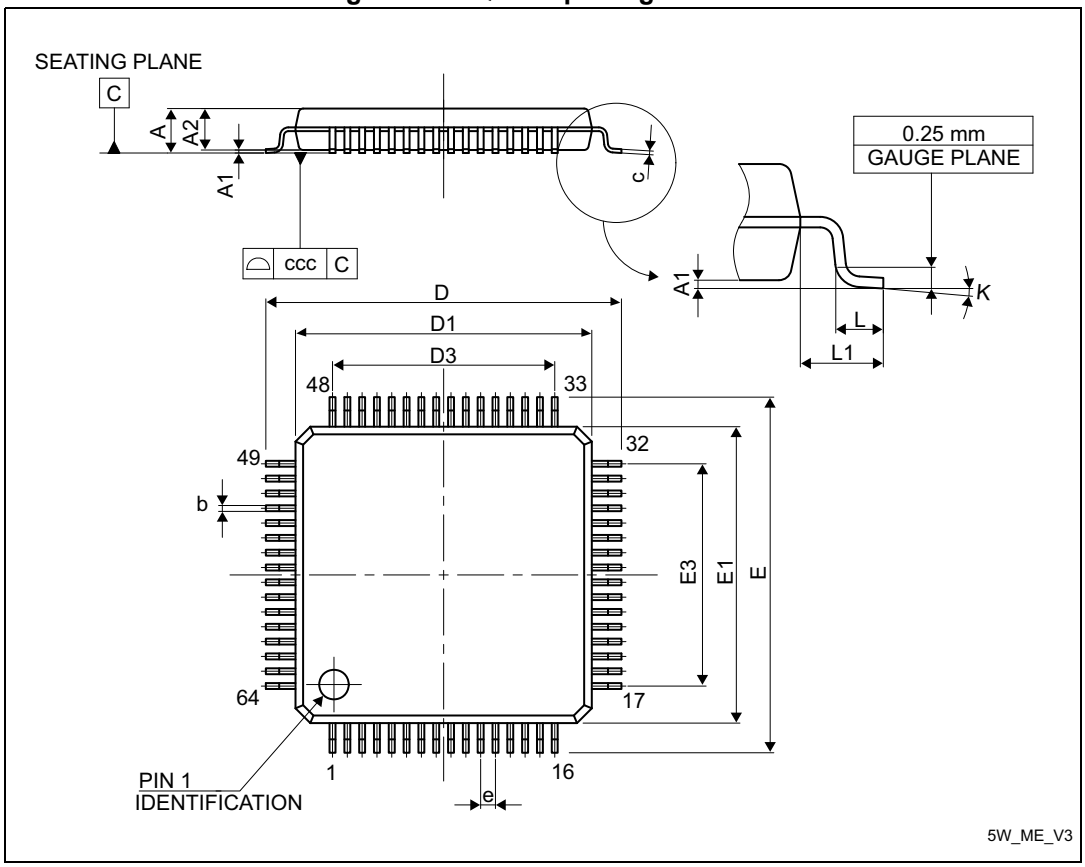
Table 66. DAC characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_{DDA}	Analog supply voltage	-	2.4	-	3.6	V
R_{LOAD}(1)	Resistive load	DAC output buffer ON (to V_{SSA})	5	-	-	kΩ
R_{LOAD}(1)	Resistive load	DAC output buffer ON (to V_{DDA})	25	-	-	kΩ
R_O(1)	Output impedance	DAC output buffer OFF	-	-	15	kΩ
C_{LOAD}(1)	Capacitive load	DAC output buffer ON	-	-	50	pF
V_{DAC_OUT}(1)	Voltage on DAC_OUT output	Corresponds to 12-bit input code (0x0E0) to (0xF1C) at V_{DDA} = 3.6 V and (0x155) and (0xEAB) at V_{DDA} = 2.4 V	0.2	-	V_{DDA} – 0.2	V
		DAC output buffer OFF	-	0.5	-	mV
			-	-	V_{DDA}– 1LSB	V
I_{DDA}(3)	DAC DC current consumption in quiescent mode(2)	With no load, middle code (0x800) on the input	-	-	380	µA
		With no load, worst code (0xF1C) on the input.	-	-	480	µA

7.4 LQFP64 package information

LQFP64 is a 64-pin, 10 x 10 mm low-profile quad flat package.

Figure 39. LQFP64 package outline



1. Drawing is not to scale.

Table 74. LQFP64 package mechanical data

Symbol	millimeters			inches[1]		
	Min	Typ	Max	Min	Typ	Max
A	-	-	1.600	-	-	0.0630
A1	0.050	-	0.150	0.0020	-	0.0059
A2	1.350	1.400	1.450	0.0531	0.0551	0.0571
b	0.170	0.220	0.270	0.0067	0.0087	0.0106
c	0.090	-	0.200	0.0035	-	0.0079
D	11.800	12.000	-	-	0.4724	-
D1	9.800	10.000	-	-	0.3937	-
E	-	12.000	-	-	0.4724	-
E1	-	10.000	-	-	0.3937	-
e	-	0.500	-	-	0.0197	-

9 Revision history

Table 77. Document revision history

Date	Revision	Changes
11-Apr-2014	1	Initial release.
9-Dec-2014	2	Updated: *Table 73: Package thermal characteristics*: remove Note 1. *Table 17: Voltage characteristics*: added line in VIN *Table 35: Low-power mode wakeup timings*: updated Max values *Table 40: HSI oscillator characteristics* (Accuracy of the oscillator) *Table 40: HSI oscillator characteristics* (Accuracy of the oscillator) *Table 54: TIMx characteristics* *Table 59: ADC characteristics* *Table 34: Peripheral current consumption* *Table 2: STM32F303x6/8 family device features and peripherals count* *Figure 17: HSI oscillator accuracy characterization results for soldered parts* Updated notes of *Table 31: Typical current consumption in Run mode, code with data processing running from Flash* and *Table 32: Typical current consumption in Sleep mode, code running from Flash or RAM*.
09-May-2015	4	Updated *Section Table 14.: STM32F303x6/8 pin definitions* and *Section Table 15.: Alternate functions*
2-Feb-2015	3	Updated: *Figure 1: STM32F303x6/8 block diagram* *Table 40: HSE oscillator characteristics* *Table 45: Flash memory characteristics* Added *Figure 13: High-speed external clock source AC timing diagram*
05-Oct-2016	5	Updated: *Section Table 66.: DAC characteristics*, *Section Table 61.: ADC characteristics*,*Table 55: NRST pin characteristics*, *Figure 2: Clock tree*,*Table 14: STM32F303x6/8 pin definitions*,*Table 68: Operational amplifier characteristics*, *Figure 20: 5V- tolerant (FT and FTf) I/O input characteristics - CMOS port*, *Table 24: Embedded internal reference voltage*, *Table 41: LSE oscillator characteristics (fLSE = 32.768 kHz)*. Added: *Table 37: Wakeup time using USART*.